





7, Autogennaya Str., Kharkov, 61099, Ukraine. Phone: (+38-057) 728-1244, 728-1241. Fax: (+38-057) 728-1243, (+38-0572) 946-830 E-mail: market@yuzhcable.com.ua

ПвЭгПу-35 1х50 ТУ У 31.3-00214534-017-2003

Power cables with copper conductors, with XLPE, longitudinal screen sealing and strengthened polyethylene outer sheath

For the cable of this mark correspond the foreign-made analogues:

Π_ΒΠγ_Γ (RU)

Technical cable requirements correspond to IEC 60502-2

Cables are used for laying:

- in soil (trenches)
- · on difficult route sections, according to the unique specification
- in the air, including cable structures, if provided the additional fire protection

It is possible to manufacture cables with extruded semiconductor layer along outer sheath.

Order entry example:

ПвЭгПу-П-35 1х50/16 ТУ У 31.3-00214534-017-2003

An extruded semiconductor layer along outer sheath ensures the correct testing of cable line with sections of underground laying in polymer pipes.

It is possible to manufacture cables with an integrated fiber-optic module.

Order entry example:

ПвЭгПу-35 1х50/16 (ОМ) ТУ У 31.3-00214534-017-2003

In conjunction with the DTS system, the integrated fiber-optic module can act as a distributed cable line temperature sensor.

It is possible to manufacture cable with sealed conductor.

Order entry example:

ПвЭгПу-35 1х50/16 (г) ТУ У 31.3-00214534-017-2003







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TECHNICAL SPECIFICATIONS

Rated voltage	kV	35
Maximum voltage	kV	42
Number and rated area of conductors	mm²	1 x 50
Insulation thikness	mm	8.6
Minimum screen cross-section	mm²	16
Permissible short circuit current across the screen of	kA	3.3
minimum cross-section		
Maximum permissible short-circuit current in core	kA	7.2
Permissible continious current rating *		
by aerial laying in trefoil formation	Α	238
by aerial flat laying	Α	286
by burial in trefoil formation	Α	196
• by burial flat	Α	203
Partial discharge factor for rated voltage, not more than	рС	6
Maximum permissible conductor temperature		
Continious	°C	+90
in emergency operation	°C	+130
• at short circuit	° C	+250
Operating temperature range	°C	-60 +50
Minimum bending radius by laying	mm	624
Rated outer diameter of the cable (for reference) **	mm	39
Cable weight (approximate)	kg/km	1380
Rated factory cable length and gross weight of the delivery	m, t	# 18аУД-40: 1062 • 2.0
on the drums		# 20aУД-60: 1244 • 2.4
Mata		

Notes:

When ordering it is neccesary to agree the factory length of the product with the manufacturer

^{*} Long permissible current loads are calculated for the following conditions: conductor temperature 90 °C, air temperature 30 °C, soil temperature 20 °C, thermal resistivity of soil 1.5 °K•m/W, laying depth in the soil 0.8 m, while laying in flat formation the distance between cables in clear is equal to the cable diameter, while laying in trefoil formation cables are laid side by side, shields are earthed on both ends of the line

^{**} The external diameter may differ from the rated up to \pm 10 %



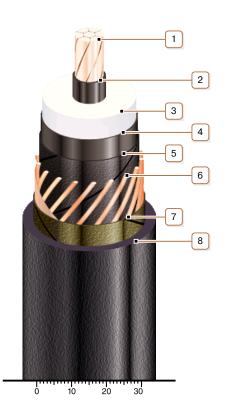




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CONSTRUCTION

1. Copper multiwire compact conductor

Note: It is possible to manufacture cable with sealed conductor.

- 2. Inner extruded semiconducting layer
- 3. XLPE insulation
- 4. Outer extruded semiconducting layer
- 5. Lapping layer of semiconductive swellable tape
- 6. Copper screen
- 7. Lapping layer of nonwoven cloth tape
- 8. Strengthened polyethylene outer sheath

Note: It is possible to manufacture cable with extruded semiconductor layer along outer sheath